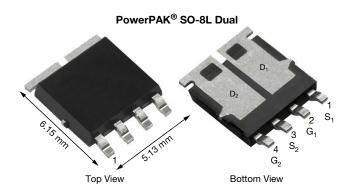


Vishay Siliconix

## Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	40
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.0110
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0120
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 2.9 \text{ V}$	0.0150
I <sub>D</sub> (A) per leg	30
Configuration	Dual
Package	PowerPAK SO-8L

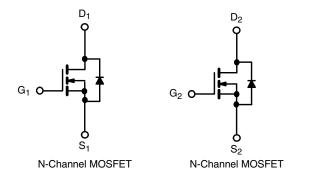
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	40	V	
Gate-source voltage		V <sub>GS</sub>	± 12		
Continuous drain current	T <sub>C</sub> = 25 °C <sup>a</sup>	· I <sub>D</sub>	30		
	T <sub>C</sub> = 125 °C		26		
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	30	Α	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	100		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	26		
Single pulse avalanche energy	L=0.11IIII	E <sub>AS</sub>	33.8	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	D	48	W	
	T <sub>C</sub> = 125 °C	$P_{D}$	16		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	00	
Soldering recommendations (peak temperature) d, e		· ·	260	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>c</sup>	$R_{thJA}$	85	°C/W	
Junction-to-case (drain)		R <sub>thJC</sub>	3.1	C/VV	

#### **Notes**

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> =	= 0 V, I <sub>D</sub> = 250 μA	40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	· V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.0	1.5	2.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 12 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	20	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 9 A	-	0.0090	0.0110	
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 9 A, T <sub>J</sub> = 125 °C	-	-	0.0181	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 9 A, T <sub>J</sub> = 175 °C	-	-	0.0222	Ω
		V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 7 A	-	0.0097	0.0120	
		V <sub>GS</sub> = 2.9 V	I <sub>D</sub> = 5 A	-	0.0121	0.0150	
Forward transconductance b	9 <sub>fs</sub>	$V_{DS}$	= 15 V, I <sub>D</sub> = 9 A	-	70	-	S
Dynamic <sup>b</sup>							•
Input capacitance	C <sub>iss</sub>			-	2255	3000	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	195	275	pF
Reverse transfer capacitance	C <sub>rss</sub>			-	82	110	
Total gate charge <sup>c</sup>	Qg			-	40	60	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_{D} = 5 \text{ A}$	-	5	-	nC
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	5	-	
Gate resistance	Rg		f = 1 MHz	0.55	1.18	1.80	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	12	20	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$	= 20 V, $R_L = 4 \Omega$	-	4	10	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D\cong$ 5 A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$		-	33	50	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	4	10	
Source-Drain Diode Ratings and Characte	ristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	100	Α
Forward voltage	$V_{SD}$	I <sub>F</sub> =	= 7 A, V <sub>GS</sub> = 0 V	-	0.79	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	29	60	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	]	۸ di/dt 100 ۸/۰۰۰	-	30	60	nC
Reverse recovery fall time	t <sub>a</sub>	I <sub>F</sub> = 5 i	A, di/dt = 100 A/μs	-	20	-	·
Reverse recovery rise time	t <sub>b</sub>			-	9	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.1	-	Α

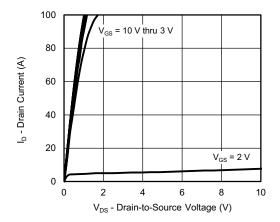
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

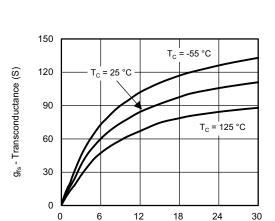
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

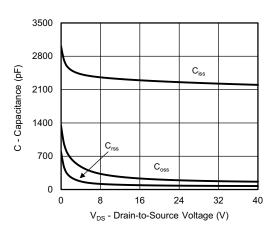


#### **Output Characteristics**

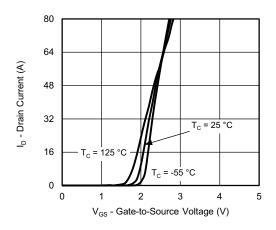


Transconductance

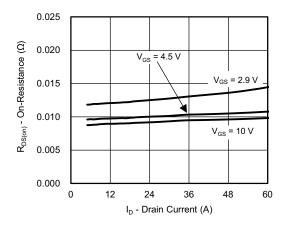
I<sub>D</sub> - Drain Current (A)



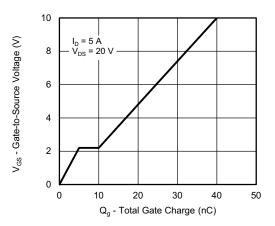
Capacitance



**Transfer Characteristics** 



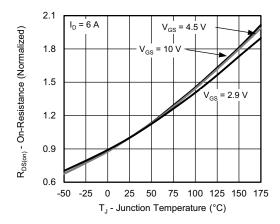
On-Resistance vs. Drain Current



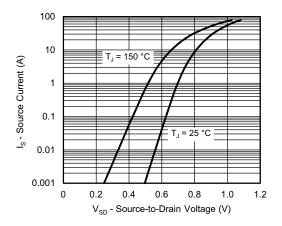
**Gate Charge** 



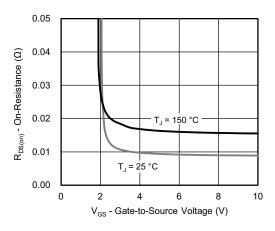
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



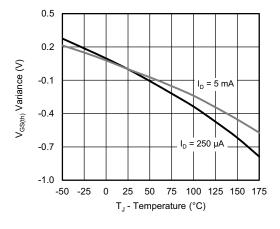
On-Resistance vs. Junction Temperature



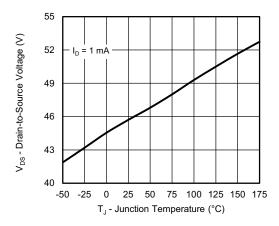
**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to-Source Voltage



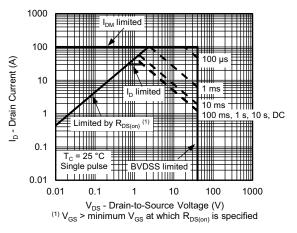
Threshold Voltage



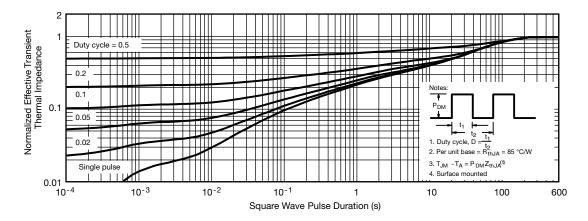
Drain Source Breakdown vs. Junction Temperature



## **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



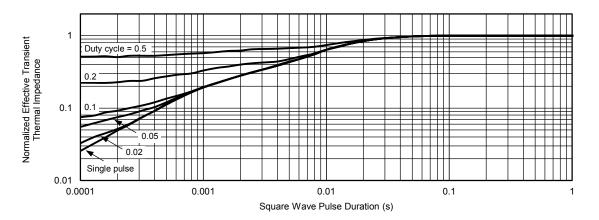
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

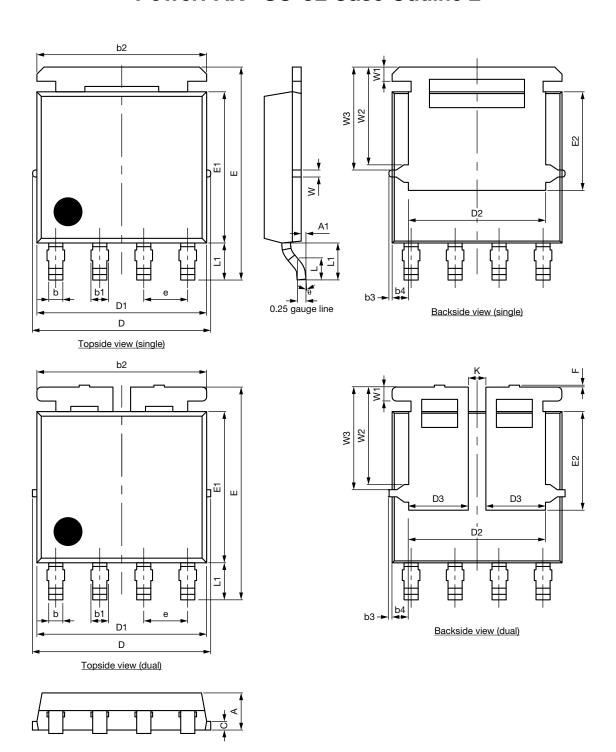
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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## PowerPAK® SO-8L Case Outline 2



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DIM.	MILLIMETERS			INCHES		
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
А	1.00	1.07	1.14	0.039	0.042	0.045
A1	0.00	-	0.127	0.00	-	0.005
b	0.33	0.41	0.48	0.013	0.016	0.019
b1	0.44	0.51	0.58	0.017	0.020	0.023
b2	4.80	4.90	5.00	0.189	0.193	0.197
b3		0.094		0.004		
b4		0.47		0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012
D	5.00	5.13	5.25	0.197	0.202	0.207
D1	4.80	4.90	5.00	0.189	0.193	0.197
D2	3.86	3.96	4.06	0.152	0.156	0.160
D3	1.63	1.73	1.83	0.064	0.068	0.072
е		1.27 BSC		0.050 BSC		
Е	6.05	6.15	6.25	0.238	0.242	0.246
E1	4.27	4.37	4.47	0.168	0.172	0.176
E2	2.75	2.85	2.95	0.108	0.112	0.116
F	-	-	0.15	-	-	0.006
L	0.62	0.72	0.82	0.024	0.028	0.032
L1	0.92	1.07	1.22	0.036	0.042	0.048
K		0.51			0.020	
W	0.23		0.009			
W1	0.41			0.016		
W2	2.82		0.111			
W3	2.96			0.117		
θ	0°	-	10°	0°	-	10°

ECN: C21-1498-Rev. C, 01-Nov-2021

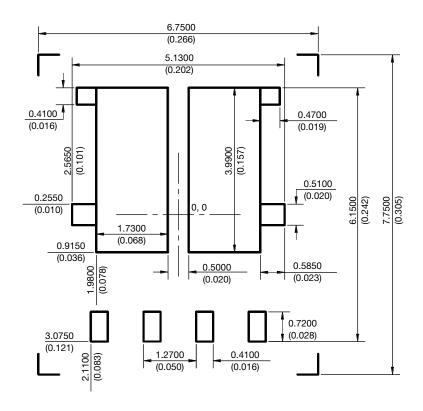
DWG: 6044

### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)



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